L	Hits	Search Text	DB	Time stamp
Number 7	. 2	heater near4 heat adj sink adj material	USPAT;	2002/12//31
			US-PGPUB;	10:15
1		:	EPO; JPO; DERWENT;	
			IBM_TDB	1
8	23	heater same heat adj sink adj material	USPAT; US-PGPUB;	2002/12/31
			EPO; JPO;	10.10
			DEFWENT;	
9	24	iii near2 nitride and (both adj side)	IBM_TDB USFAT;	2002/12-31
		same deposit\$4	US-PGPUB;	10:20
		•	EPO; JPO;	
1	1		DEPWENT; IBM TDB	
10	78	The state of the s	USFAT;	2002/12/31
		same deposit\$4	US-PGPUB;	10:25
			EPO; JPO; DEPWENT;	
:			IBM_TDB	
11	96	<pre>double near2 sid\$2 near2 (epitax\$4 or deposit\$4)</pre>	USFAT; US-PGFUB;	2002/12/31 10:27
		doposito; 1,	EPO; JPO;	19.27
			DEPWENT;	
14	. 4	(double near2 sid\$2 near2 (epitax\$4 or	IBM_TDB USPAT;	2002/12/31
		deposit\$4)) and 117/\$4.ccls.	US-PGFUB;	10:37
			EPO; JPO; DEFWENT;	i
			IBM TDB	i i
-	2	(layer\$3 same substrate same (gan or	USFĀT;	2002/12/23
		gallium adj nitride or sapphire or zinc adj oxide or zno or silicon adj carbide	US-PGFUB; EPO; JPO;	16:00
		or silicon or si or sic) and two near2	DEFWEIT;	1
:		sid\$3 same deposit\$4) and 117/84-109.ccls.	IBM_TDB	·
-	15	two near2 layer\$3 near3 substrate near4	USPAT;	2002/12/23
		(gan or gallium adj nitride or sapphire	US-PGFUB;	16:12
	1	or zinc adj oxide or zno or silicon adj carbide or silicon or si or sic) and	EPO; JPO; DEPWENT;	
		117/\$4.ccls.	IBM_TDB	
: =	38	multi\$1layer\$3 near3 substrate and 117/\$4.ccls. and (remov\$3 near2	USFAT;	2002/12/23 16:20
!	:	substrate)	US-PGPUB; EPO; JPO;	10.20
			DEPWENT;	
: -	2	two near1 sid\$3 near4 deposit\$4 and	IBM_TDB USFAT;	2002/12/23
		117/\$4.ccls.	US-PGPUB;	16:49
			EPO; JPO; DEPWENT;	
			IBM_TDB	
· _	. 66	(both or two) near1 sid\$3 same deposit\$4 and 117/\$4.ccls.	USFAT; US-PGFUB;	2002/12/30
!		and 117/\$4.CCIS.	EPO; JPO;	10.10
1		I	DEFWENT;	
: ! -	10	(both or two) nearl sid\$3 same deposit\$4	IBM_TDB USFAT;	2002/12/23
	, 10 !	and 117/\$4.ccls. and "III-V"	US-PGPUB;	17:07
ļ 1			EPO; JPO; DEFWENT;	[
			IBM TOB	
_	31	"III-v" same deposit\$4 and (both or two)	USFAT;	2002/12/23
		near3 (side or sided) and 117/\$4.ccls.	US-PGPUB; EPO; JPO;	17:15
	ļ		DERWENT;	
			IBM_TDB	

i -	11	. (gan or gallium adj nitride) near2	USPAT;	2002/12/23
		sapphire near3 (silicon or si) and	US-PGPUB;	17:20
	:	117/\$4.ccls.	EPO; JPO;	. 1, 120
!			DERWENT;	ļ.
	. 40		IBM_TDB	İ
: -	43	((sapphire or "al.sub.2o.sub.3") near3	USPAT;	2002/12/30
		(silicon or si) near3 (substrate or	US-PGPUB;	10:11
		wafer) and 117/\$4.ccls.) and "III-V"	EPO; JPO;	i
			DERWENT;	
: -	19	(sapphire or "al.sub.20.sub.3") near2	IBM_TDB	
1	1	buffer and 117/\$4.ccls.	USPAT;	2002/12/30
i		THE THE TIME THE TENT OF THE T	US-PGPUB; EPO; JPO;	10:18
	1		DEFWENT;	
İ			IBM TDB	
-	23	(sapphire or "al.sub.2o.sub.3") near2	USPAT;	2002/12/30
		buffer near3 (silicon or si or zinc adi	US-PGPUB;	10:24
i		oxide or zno or sic or silicon adj	EPO; JPO;	
	İ	carbide or "III-V")	DEPWENT;	
			IBM_TDB	
-	9	(sapphire same "al.sub.2o.sub.3") and	USFAT;	2002/12/30
		117/\$4.ccls.	US-PGPUB;	13:24
			EPO; JPO;	
			DEPWENT;	
_	4	sacrific\$3 near2 substrate same (sapphire	IBM_TDB	
	3	or "al.sub.20.sub.3") and 117/\$4.ccls.	USPAT;	2002/12/30
		al.3ub.20.5ub.5 and 11//\$4.CCIS.	US-PGPUB;	13:27
			EPO; JPO; DERWENT;	
			IBM TDB	
_	31	remov\$4 near2 substrate same (sapphire or	USPAT;	2002/12/30
i		"al.sub.20.sub.3") and 117/\$4.ccls.	US-PGPUB;	13:51
I		1	EPO; JPO;	1 13.31
			DERWENT;	
-		; 	IBM TDB	
-	39		USPĀT;	2002/12/30
	i	near2 substrate and 117/\$4.ccls.) and	US-PGPUB;	13:58
		"iii-v"	EPO; JPO;	
			DERWENT;	
i _		gambine rame (mulbilessed2)	IBM_TDB	
	, I	sapphire same (multilayer\$3) near2 substrate and 117/\$4.ccls.	USFAT;	2002/12/30
	i	substrace and 11//54.ccis.	US-PGPUB;	14:00
			EPO; JPO; DEPWENT;	
			IBM TDB	
-	3	sapphire same (layered) near2 substrate	USPAT;	2002/12/30
		and 117/\$4.ccls.	US-PGPUB;	14:06
			EPO; JPO;	
1			DEPWENT;	
	ļ		IBM_TDB	
-	10	(sapphire or "al.sub.2o.sub.3") near2	USPAT;	2002/12/30
		substrate and ("iii-v") and both near2	US-PGPUB;	14:36
İ		side and 117/\$4.ccls.	EPO; JPO;	
			DEPWENT;	ĺ
1 _		hoth many aids10 des 1144	IBM_TDB	1 2 2 2 2 7 1 2 7 2 2
_	. 3	both near2 side near10 deposit\$4 and	USPAT;	2002/12/30
i		"iii-v" and 117/\$4.ccls.	US-PGPUB;	14:38
	!		EPO; JPO; DERWENT;	
į			DERWENT; IBM TDB	
! -	30	both near2 side same (deposit\$4 or	USPAT;	2002/12/30
!		grow\$4) and "iii-v" and 117/\$4.ccls.	US-PGPUB;	14:39
	İ		EPO; JPO;	
1			DERWENT;	
l		Í	IBM TDB	
-	102	selectiv\$4 near2 etch\$3 near5 substrate	USPĀT;	2002/12/30
		and 117/\$4.ccls.	US-PGPUB;	15:24
	1		EPO; JPO;	
			DERWENT;	
			IBM_TDB	

_		23 (selectiv\$4 near2 etch\$3 near5 substrate	USPAT;	2002/12/30	
		and 117/\$4.ccls.) and "iii-v"	US-PGPUB;	16:11	1
			EPO; JPO;		
			DEPWENT;	•	- :
1	1		IBM_TDB		
; -		11 (both or two) nearl sid\$3 same deposit\$4	USFAT;	2002/12/30	1
1		same epitax\$4 and 118/\$4.ccls.	US-PGPUB;	16:22	į
1			EPO; JPO;		1
			DEPWENT;	1	1
	:		IBM_TDB		
; -		14 ((both or two) nearl sid\$3 near3	USPAT;	2002/12/30	
		(deposit\$4 or grow\$4) and 118/\$4.ccls.)	US-PGPUB;	16:43	
		and (epitax\$4 or single adj crystal\$4)	EPO; JPO;		
			DEFWENT;		
			IBM TDB		
-		25: (front near2 side and back near2 side)	USFAT;	2002/12/30	
		same (deposit\$4 or grow\$4) and	US-PGPUB;	16:48	:
		117/\$4.ccls.	EPO; JPO;		
			DEFWENT;	İ	
			IBM_TDB		
		67 heat adj sink adj material same radiat\$4	USPAT;	2002/12/30	
			US-PGFUB;	18:21	+
			EPO; JPO;		İ
			DEFWENT;		i
			IBM_TDB		
-		1 without near4 heat adj sink adj material	USFAT;	2002/12/30	
		same radiat\$4	US-PGPUB;	18:22	
			EPC; JPO;		
			DEPWENT;	!	
•			IBM TDB	1	
-		7 without near4 heat adj sink adj material	USPĀT;	2002/12/31	
1			US-PGPUB;	10:13	
1			EPO; JPO;		i
	!		DERWENT;		
			IBM TDB		